# 2SB935, 2SB935A

### Silicon PNP epitaxial planar type

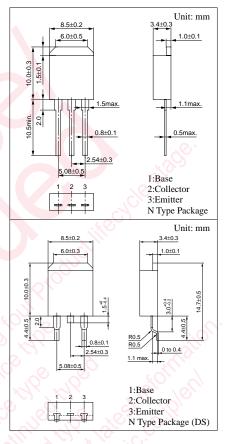
For low-voltage switching

#### Features

- ullet Low collector to emitter saturation voltage  $V_{CE(sat)}$
- High-speed switching
- N type package enabling direct soldering of the radiating fin to the printed circuit board, etc. of small electronic equipment.

#### Absolute Maximum Ratings $(T_C=25^{\circ}C)$

Parameter		Symbol	Ratings	Unit	
Collector to	2SB935	3.7	-40	v	
base voltage	2SB935A	$V_{CBO}$	-50		
Collector to	2SB935	V	-20	V	
emitter voltage	2SB935A	$V_{CEO}$	-40	v	
Emitter to base voltage		$V_{\rm EBO}$	-5	V	
Peak collector current		$I_{CP}$	-15	A	
Collector current		$I_{\rm C}$	-10	A	
Collector power	T <sub>C</sub> =25°C	D	35	777	
dissipation	Ta=25°C	$P_{C}$	1.3	W	
Junction temperature		$T_{j}$	150	°C	
Storage temperature		$T_{stg}$	-55 to +150	°C .	



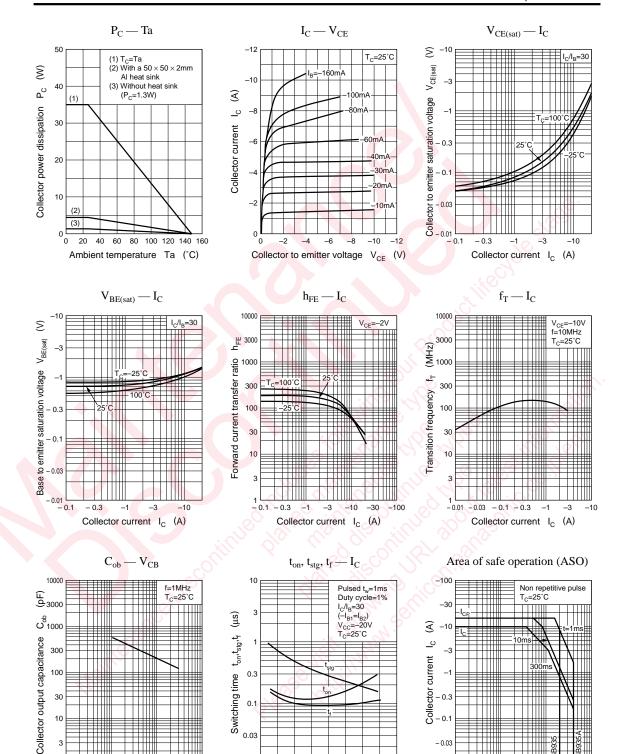
#### ■ Electrical Characteristics (T<sub>C</sub>=25°C)

Parameter		Symbol	Conditions	min	typ	max	Unit
Collector cutoff	2SB935		$V_{CB} = -40V, I_{E} = 0$	0	05	-50	
current	2SB935A	$I_{CBO}$	$V_{CB} = -50V, I_E = 0$	Y 20		-50	μΑ
Emitter cutoff current		$I_{EBO}$	$V_{EB} = -5V, I_C = 0$	W. Y.		-50	μΑ
Collector to emitter	2SB935	V <sub>CEO</sub>	$I_{\rm C} = -10 {\rm mA}, I_{\rm B} = 0$	-20			V
voltage	2SB935A			-40			
Forward current transfer ratio		h <sub>FE1</sub>	$V_{CE} = -2V, I_C = -0.1A$	45			
		h <sub>FE2</sub> *	$V_{CE} = -2V, I_{C} = -2A$	90		260	
Collector to emitter saturation voltage		V <sub>CE(sat)</sub>	$I_C = -7A$ , $I_B = -0.23A$			- 0.6	V
Base to emitter saturation voltage		V <sub>BE(sat)</sub>	$I_C = -7A$ , $I_B = -0.23A$			-1.5	V
Transition frequency		$f_T$	$V_{CE} = -10V$ , $I_{C} = -0.5A$ , $f = 10MHz$		150		MHz
Collector output capacitance		C <sub>ob</sub>	$V_{CB} = -10V, I_E = 0, f = 1MHz$		200		pF
Turn-on time		t <sub>on</sub>			0.1		μs
Storage time		t <sub>stg</sub>	$I_C = -2A$ , $I_{B1} = -66mA$ , $I_{B2} = 66mA$		0.5		μs
Fall time		$t_{\rm f}$			0.1		μs

#### \*h<sub>FE2</sub> Rank classification

Rank	Q	P
h <sub>FE2</sub>	90 to 180	130 to 260

Panasonic



0.3

- 0.1

- 0.03

-0.01 -0.3

Collector to emitter voltage  $V_{CE}$  (V)

Collector to base voltage  $\ V_{CB} \ (V)$ 

0.1

0.03

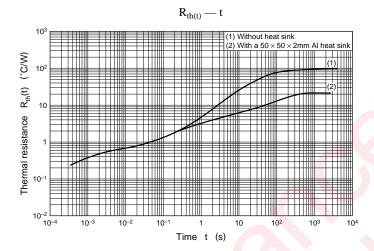
0.01 \_0

-3 -4

Collector current I<sub>C</sub> (A)

30

10



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